

150W, 50V, 175MHz N-CHANNEL RF POWER VERTICAL MOSFET

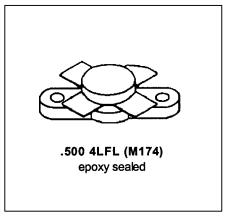
PRELIMINARY INFORMATION

VRF151

BROADBAND HF/VHF VERTICAL D-MOS ISM & MILITARY/COMMERCIAL COMMUNICATIONS APPLICATIONS

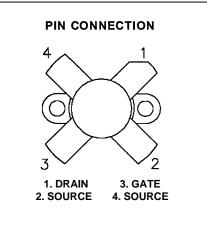
Features

- 150W WITH 14dB TYPICAL GAIN @ 175MHz, 50V
- 150W WITH 22dB TYPICAL GAIN @ 30MHz. 50V
- EXCELLENT STABILITY & LOW IMD
- COMMON SOURCE CONFIGURATION
- 30:1 LOAD VSWR CAPABILITY AT SPECIFIED OPERATING CONDITIONS
- NITRIDE PASSIVATED
- REFRACTORY GOLD METALLIZATION



DESCRIPTION:

The VRF151 is a gold metallized silicon, n-channel RF power transistor designed for broadband commercial and military applications requiring high power and gain without compromising reliability, ruggedness, and intermodulation distortion.



ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain-Source Voltage	125	V
V_{DGO}	Drain-Gate Voltage	125	V
V_{GS}	Gate-Source Voltage	±40	V
I _D	Drain Current	16	Α
P _{DISS}	Total Device Power Dissipation	300	W
TJ	Max Operating Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

R _{è(J-C)}	Thermal Resistance Junction-Case	0.6	°C/W
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ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Cymphol	Took Comditions			Value					
Symbol	Test Conditions			Min.	Тур.	Max.	Unit		
Off Characte	Off Characteristics:								
V _{(BR)DSS}	$V_{GS} = 0V$	$I_{DS} = 100mA$		125			V		
I _{DSS}	$V_{GS} = 0V$	$V_{DS} = 50V$				5.0	mA		
I _{GSS}	$V_{GS} = 20V$			1.0	μ Α				
On Characte	On Characteristics:								
$V_{GS(Q)}$	V _{DS} = 10V	$I_D = 250 mA$		1.0	3.0	5.0	V		
V _{DS(ON)}	V _{GS} = 10V	$I_D = 10A$		1.0	2.0	5.0	V		
G _{FS}	$V_{DS} = 10V$ $I_D = 250mA$			5.0			mho		
Dynamic Characteristics:									
C _{ISS}	V _{GS} = 0V	V _{DS} = 50V	f = 1 MHz		400		pF		
Coss	V _{GS} = 0V	V _{DS} = 50V	f = 1 MHz		235		pF		
C _{RSS}	$V_{GS} = 0V$	V _{DS} = 50V	f = 1 MHz		18		рF		

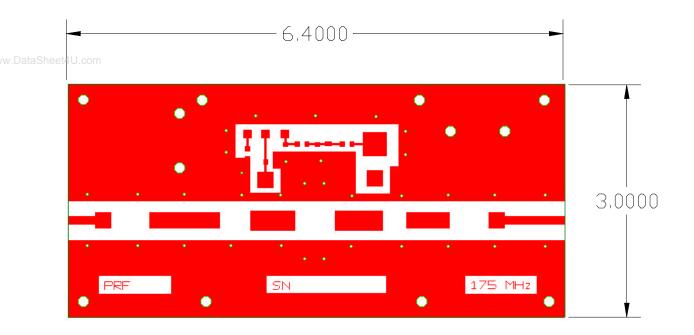
FUNCTIONAL TESTS

Symbol	Test Conditions		Value		
Syllibol	rest conditions	Min.	Typ.	Max.	Unit
P_{OUT}	$f = 175MHz$ $V_{DD} = 50V$ $I_{DQ} = 250mA$	150			W
G _{PS}	$f = 175MHz$ $V_{DD} = 50V$ $P_{OUT} = 150W_{PEP}$ $I_{DQ} = 250mA$		14		dB
G _{PS}	$f = 30MHz$ $V_{DD} = 50V$ $P_{OUT} = 150W_{PEP}$ $I_{DQ} = 250mA$	18	22		dB
η_{D}	$f = 175MHz$ $V_{DD} = 50V$ $P_{OUT} = 150W_{PEP}$ $I_{DQ} = 250mA$		55		%
IMD _(d3)	$f1 = 30MHz$ $f2=30.001MHz$ $P_{OUT} = 150W_{PEP}$ $V_{DD} = 50V$ $I_{DQ} = 250mA$		-32		dBc
Load Mismatch	$f = 30MHz$ $V_{DD} = 50V$ $P_{OUT} = 150W_{PEP}$ $V_{DQ} = 250mA$ $30:1$ VSWR - All Phase Angles	No degradation in Output Power			



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TEST CIRCUIT INFORMATION



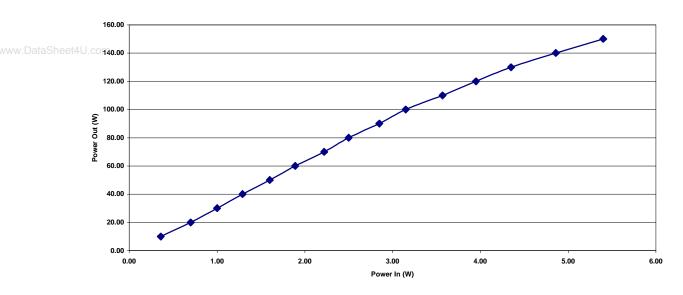




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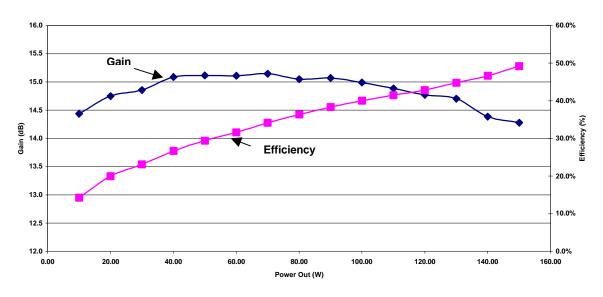
Power Out vs. Power In

Freq = 175 MHz, Vdd = 50V, IDQ = 250mA



Gain & Efficiency vs. Power Out

Freq = 175 MHz, Vdd = 50V, IDQ = 250mA

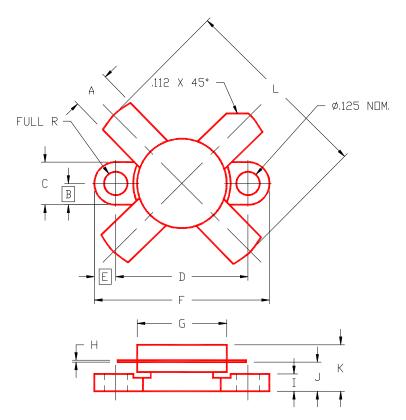




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PACKAGE MECHANICAL DATA

PACKAGE STYLE M174



	MINIMUM	MAXIMUM			MINIMUM	MAXIMUM
	INCHES/MM	INCHES/MM			INCHES/MM	INCHES/MM
Α	.220/5,59	.230/5,84		I	.090/2,29	.110/2,79
В	.125/3,18			J	.160/4,06	.175/4,45
С	.245/6,22	.255/6,48		К		.280/7,11
D	.720/18,28	.730/18,54		L		1.050/26,67
Е	.125/3,18					
F	.970/24,64	.980/24,89				
G	.495/12,57	.505/12,83				
Н	.003/0,08	.007/0,18				